

Prof.Dr. ŞEMSETTİN ALTINDAL

Kişisel Bilgiler

E-posta: altundal@gazi.edu.tr

Web: <https://avesis.gazi.edu.tr/altundal>

Eğitim Bilgileri

Doktora, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), Türkiye 1986 - 1994

Yüksek Lisans, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Türkiye 1983 - 1985

Lisans, Fırat Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1978 - 1982

Yaptığı Tezler

Doktora, Al-siox-psi aygıtların ve güneş pillerinin elektriksel karakteristikleri, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), 1993

Yüksek Lisans, Çok ince yapı teorisi, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1950

Akademik Unvanlar / Görevler

Prof.Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 2011 - Devam Ediyor

Doç.Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 2005 - 2011

Yrd.Doç.Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 1994 - 2005

Araştırma Görevlisi, Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 1983 - 1994

Yönetilen Tezler

ALTINDAL Ş., Photovoltaic and temperature Characteristics of the designed Schottky barrier diodes (SBDs) as a function of temperature and illumination, Doktora, H.MELOUD(Öğrenci), 2021

ALTINDAL Ş., Au/(nanografıt-PVP)/n-Si (MPS) yapıların hazırlanması ve elektrik ile dielektrik özelliklerinin geniş bir frekans ve voltaj aralığında incelenmesi, Doktora, A.MUHAMMED(Öğrenci), 2021

ALTINDAL Ş., Dielektrik çok katmanlı geniş bantlı kızılötesi metamalzeme soğurucunun tasarımı, üretimi ve karakterizasyonu, Doktora, B.AKIN(Öğrenci), 2021

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin frekans ve voltaja bağlı incelenmesi, Doktora, Ö.SEVGİLİ(Öğrenci), 2020

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) SCHOTTKY ENGEL DİYOTLARIN HAZIRLANMASI VE ELEKTRİK İLE DİELEKTRİK ÖZELLİKLERİNİN FREKANS VE VOLTAJA BAĞLI İNCELENMESİ, Doktora, Ö.SEVGİLİ(Öğrenci), 2020

ALTINDAL Ş., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Yüksek Lisans, S.KOÇYİĞİT(Öğrenci), 2017

ALTINDAL Ş., USLU İ., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Yüksek Lisans, S.KOÇYİĞİT(Öğrenci), 2017

ALTINDAL Ş., Polimer arayüzey tabakalı ve tabakasız schottky engel diyotların elektriksel karakteristiklerinin karşılaştırılması, Doktora, Ç.BİLKAN(Öğrenci), 2016

ALTINDAL Ş., Polimer arayüzey tabakalı ve tabakasız schottky engel diyotların elektriksel karakteristiklerinin karşılaştırılması, Doktora, Ç.BİLKAN(Öğrenci), 2016

ALTINDAL Ş., Au/n-GaAs Schottky diyotların hazırlanması ve akım-iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, E.ÖZAVCI(Öğrenci), 2015

ALTINDAL Ş., Au/Ca₃Co₄Ga_{0,001}Ox/n-Si yapılarında doğru ve ters beslem akım-voltaj (I-V) karakteristiklerinin 80-340 K sıcaklık aralığında incelenmesi, Doktora, E.MARIL(Öğrenci), 2015

ALTINDAL Ş., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Yüksek Lisans, A.AYTİMUR(Öğrenci), 2015

ALTINDAL Ş., USLU İ., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Yüksek Lisans, A.AYTİMUR(Öğrenci), 2015

ALTINDAL Ş., Au/ZnO/n-GaAs (MIS) Schottky engel diyotların (SBDs) elektriksel karakteristiklerinin frekans ve voltaja bağlı incelenmesi, Yüksek Lisans, B.AKIN(Öğrenci), 2015

ALTINDAL Ş., Au/(%1 Grafen Katkılı)-Ca_{1.9}Pr_{0.1}Co₄Ox/N-Si Schottky Engel Diyotların Hazırlanması Ve Elektrik ile Dielektrik Özelliklerinin Sıcaklık Ve Frekansa Bağlı incelenmesi, Doktora, H.Gökçen(Öğrenci), 2015

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ALTINDAL Ş., USLU İ., Grafen, bor ve nadir toprak elementleriyle katkılanmış poliviniliden florür nanokompozit piezo malzemelerin üretimi ve karakterizasyonu, Yüksek Lisans, Y.BADALÍ(Öğrenci), 2015

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ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS) yapıların hazırlanması ve temel elektriksel özelliklerinin ışık altında incelenmesi, Doktora, U.AYDEMİR(Öğrenci), 2014

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ALTINDAL Ş., Au/n-4H-SiC (MS) schottky diyotların hazırlanması ve elektriksel karekteristiklerinin frekansa bağlı incelenmesi, Yüksek Lisans, Ö.SEVGİLİ(Öğrenci), 2013

ALTINDAL Ş., Metal-polimer-yarıiletken (MPS) yapıların elektrik ve dielektrik özelliklerinin geniş frekans aralığında incelenmesi, Doktora, A.KAYA(Öğrenci), 2013

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ALTINDAL Ş., (Ni/Au)/Al_{0.22}Ga_{0.78}N/AlN/GaN çoklu-yapıların elektriksel karakteristiklerinin admitans spektroskopisi yöntemiyle incelenmesi, Doktora, Y.ŞAFAK(Öğrenci), 2012

ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS)schottky engel diyodun elektriksel özelliklerinin sıcaklık ve radyasyona bağlı incelenmesi, Doktora, İ.TAŞÇIOĞLU(Öğrenci), 2012

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO₂/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve

potansiyeye bağılı incelenmesi, Doktora, Z.SÖNMEZ(Öğrenci), 2012

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO₂/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve potansiyeye bağılı incelenmesi, Doktora, Z.SÖNMEZ(Öğrenci), 2012

ALTINDAL Ş., (Ni/Au)/Al_{0.22}Ga_{0.78}N/AlN/GaN çoklu-yapıların elektriksel karakteristiklerinin admitans spektroskopisi metoduyla incelenmesi, Doktora, Y.ŞAFAK(Öğrenci), 2012

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ALTINDAL Ş., Au/SiO₂/n-Si (MIS) yapının elektrik ve dielektrik karakteristiklerinin sıcaklığa bağılı incelenmesi, Yüksek Lisans, A.GÜL(Öğrenci), 2011

ALTINDAL Ş., Al / Rhodamine - 101 / n-GaAs Schottky Engel diyotlarının hazırlanması ve iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, Ö.VURAL(Öğrenci), 2011

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ALTINDAL Ş., Au/(Bi-katkılı) polivinil alkol/n-si schottky engel diyotlarının elektriksel özelliklerinin sıcaklığa ve aydınlatma şiddetine bağılı incelenmesi, Yüksek Lisans, H.GÖKÇEN(Öğrenci), 2011

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ALTINDAL Ş., Al/SiO₂/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağılı incelenmesi, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., Al/SiO₂/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağılı incelenmesi, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağılı incelenmesi, Doktora, H.USLU(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.5}N/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağılı incelenmesi, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.5}N/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağılı incelenmesi, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., SiO₂/p-Si (MIS) YAPILARIN ELEKTRİK KARAKTERİSTİKLERİNİN FREKANS BAĞLI İNCELENMESİ, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.5}N/GaN HETEROYAPILARIN ELEKTRİKSEL KARAKTERİSTİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağılı incelenmesi, Doktora, H.USLU(Öğrenci), 2010

ALTINDAL Ş., Au/SrTiO₃/n-Si (MFS) Schottky diyotların elektriksel parametrelerinin I-V, C-V ve DLTS metodu ile incelenmesi, Yüksek Lisans, U.AYDEMİR(Öğrenci), 2009

ALTINDAL Ş., Au/SrTiO₃/n-Si (MFS) Schottky diyotların elektriksel parametrelerinin I-V, C-V ve DLTS metodu ile incelenmesi, Yüksek Lisans, U.AYDEMİR(Öğrenci), 2009

ALTINDAL Ş., Yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin sıcaklığa bağılı incelenmesi, Doktora, H.KANBUR(Öğrenci), 2008

ALTINDAL Ş., Au/SiO₂/n-GaAs (MOY) YAPILARIN ELEKTRİK VE DİELEKTRİK KARAKTERİSTİKLERİNİN FREKANS VE SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, M.GÖKÇEN(Öğrenci), 2008

ALTINDAL Ş., Al/ SiO₂/p-Si (MY) YAPILARIN AKIM-İLETİM MEKANİZMASI VE ELEKTRİKSEL ÖZELLİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, D.Esra(Öğrenci), 2008

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ALTINDAL Ş., Au/SiO₂/n-GaAs (MOY) yapıların elektrik ve dielektrik karakteristiklerinin frekans ve sıcaklığa bağılı incelenmesi, Doktora, M.GÖKÇEN(Öğrenci), 2008

ALTINDAL Ş., Au/SiO₂/n-GaAs (MOY) yapıların elektrik ve dielektrik karakteristiklerinin frekans ve sıcaklığa bağlı incelenmesi, Doktora, M.GÖKÇEN(Öğrenci), 2008

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ALTINDAL Ş., Au/Bi₄Ti₃O₁₂/SiO₂/n-Si yapıların hazırlanması, elektriksel ve dielektrik özelliklerinin frekans ve sıcaklığa bağlı incelenmesi, Doktora, F.PARLAKTÜRK(Öğrenci), 2007

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ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Schottky diyotların elektriksel özelliklerinin frekans ve aydınlanma şiddetine bağlı incelenmesi, Yüksek Lisans, M.HAMDİ(Öğrenci), 2007

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ALTINDAL Ş., MIS yapıların frekans ve radyasyona bağlı temel elektriksel parametreleri, Yüksek Lisans, B.TATAROĞLU(Öğrenci), 2006

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ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Schottky diyotlarının sıcaklığa bağlı temel parametreleri, Yüksek Lisans, E.MARIL(Öğrenci), 2005

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ALTINDAL Ş., MOS yapılarda temel fiziksel parametrelerin frekans ve radyasyon miktarına bağlı incelenmesi, Doktora, A.TATAROĞLU(Öğrenci), 2004

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ALTINDAL Ş., Yalıtkan arayüzey tabakası ve seri dirence sahip Al/ SnO₂/ p-Si schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Yüksek Lisans, Z.TEKELİ(Öğrenci), 2002

ALTINDAL Ş., Al/p-Si ve Au/n-Si schottky diyotlarda I-V ve C-V karakteristiklerinin geniş bir sıcaklık aralığında analizi,

Doktora, İ.DÖKME(Öğrenci), 2002

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ALTINDAL Ş., Güneş pillerinde arayüzey durumlarının c.v. karakteristiklerine etkisi, Yüksek Lisans, E.YILDIZ(Öğrenci), 1999

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Demirezen S., Ozavci E., Altindal Ş.

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Tascioglu I., Farooq W. A. , TURAN R., ALTINDAL Ş., YAKUPHANOĞLU F.

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